METHOD OF MAKING A VERTICAL ELECTRONIC DEVICE

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ABSTRACT

A semiconductor substrate having had a semiconductor device formed on the front side of the semiconductor substrate is subjected to an ion implant on the back side of the semiconductor substrate. The active surface of the doped back side is controllably heated to perform an implant anneal. The implant anneal of the back side of the semiconductor substrate is performed using a flash anneal process which avoids causing the destruction of the semiconductor device formed on the front side of the semiconductor substrate.